PMT Mask-less exposure apparatus PLS-3000

Apparatus appearance



PMT Mask-less exposure apparatus PLS-3000 Specification

Equipment	Name		Mask-less Exposure Apparatus
Summary	Model		PLS-3000
	Dimensions (Including		W 1,550 mm × D 1,450 mm × H 2,000 mm
	body	thermal	, , , , , , , , , , , , , , , , , , , ,
		chamber)	
		Control unit	W 600 mm × D 650 mm × H 900 mm
	Mass body	(Including	Approx. 1,500 kg
		thermal	
		chamber)	
		Control unit	Approx. 100 kg
Work piece	Size		Diameter 300 mm, Thickness 0.5~7 mm
-	Supply system		Manual
	Fixing system		Vacuum adsorption
Capability	Throughput		Approx. 530 minutes / sheet
			[Normal exposure 12inch entire surface of the
			wafer drawing]
	Maximum exposure rate		180 mm ² /min (transport, AF, does not include
			such alignment time)
	Exposure speed setting range		0.1 mm/sec ~ 3.75 mm/sec
	Positioning system		The semi-automatic alignment by image
			recognition
	Overlay accuracy		Within X,Y ±1µm
	Data resolution		0.5µm/pixel
	Exposure resolution		1.0µm (1:1 Line & Space)
	Minimum line wi	dth	0.5µm (single line)
	Swath junction co		Within ±0.5μm
	Evaluation conditions		Work piece: 4 inch silicon wafer
			Resist: Tokyo Ohka Kogyo (Co.) OFPR-5000
			Resist film thickness: 1µm
Exposure Syst	Exposure system		The scan exposure by synchronous scanning of DMD and stage
	Spatial light modulation element		1,920×1,080 pixels
			it uses only part of the exposure (generally
			about 20%)
	Exposing source		LED
	Peak wavelength		405 nm
	Maximum exposure energy		950 m W/cm ² and more
	Objective numeri	cal aperture	0.4
	Reduction ratio		1/21.6
	Minimum pixel s	ize	0.5µm/pixel
Alignment	Camera		CMOS image sensor
system	Illumination ligh	t source	LED

	Peak wavelength			625 nm	
Focal point	Drawing before the start			Contrast type auto focus	
Adjustment	After drawing start			The dynamic focus by a laser displacement	
				meter	
				Correction follow-up range: ± 10µm	
				Laser peak wavelength: 650 nm	
Machinery	Axis configuration			X-Y-Z-θ 4 axis	
Specification	Stroke X Z θ		XY	300 mm×300 mm	
			Z	7 mm	
				±3 deg	
	The anti-vibration mechanism		nanism	Stone surface plate + air spring passive vibration isolation	
Power	Required electric capacity			Single-phase 100 V 15 A	
Supply	Consumption Body			400 W	
	1 - 1	Vacuum pump		600 W	
	*for data corruption and exposure in loss avoidance of the wafer at the time of				
	power outage				
	(Uninterruptible power supply) Built-in UPS				
	*Storage battery is being used must be replaced periodically (approximately				
	every 4-5 years)				
Air pressure	Supply pressure			0.45 MPa ~ 0.8 MPa	
	Supply flow rate			Maximum: less 50 Nl/min	
	E and			Drawing during: 40: less Nl/min	
	[ISO / DIS 5598 temperature 20 $^{\circ}\text{C}$ / absolute pressure 101.3 kPa / relative humidity 65% (ANR)]				
	Atmospheric pressure dew point			-10 ℃ below	
				(However, the room temperature is not below	
				freezing)	
	Compressed air cleanliness			Fine solids 0.3µm or less	
				Oil mist removal rate of 99.99% or more	
	Connection			Φ6 mm one-touch coupler	
Vacuum	Vacuum source			Diaphragm type dry vacuum pump	
	Installation location			Place floor to the outside of the apparatus	
	The effective pumping speed			100 L/min	
	* regular basis, such as exchange of the diaphragm must be overhauled to				
	(almost every year) *Recommende				
Installation	Temperature			23 ± 1 °C (during operation)	
Environment	TT 11,			during non-operation, transportation time)	
	Humidity			6RH(non-condensing)	
	Cleanliness			ss 6 (Class 1000) or more	
	Lighting			does not contain a photosensitive wavelength of	
	use resi (Vollow		(Yellow		
			+	s no vibration, and installed in a robust floor	
				ration source Without that close exposure device	
	cuvii omment		1 1116 (10)	ranon source without mat close exposure device	

